
HL8325G

GaAlAs Laser Diode



ODE-208-582C (Z)

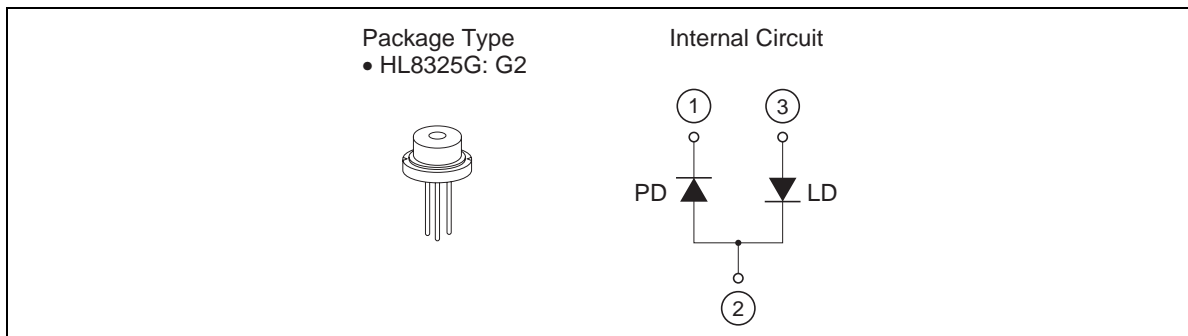
Rev.3
Mar. 2005

Description

The HL8325G is a high-power 0.8 μm band GaAlAs laser diode with a TQW (triple quantum well) structure. Its internal circuit configuration is suitable for operation on a single positive supply voltage. It is suitable as a light source for optical disk memories, card readers and various other types of optical equipment.

Features

- Infrared light output: $\lambda_p = 820$ to 840 nm
- High power: standard continuous operation at 40 mW (CW), pulsed operation at 50 mW
- Built-in monitor photodiode
- Single longitudinal mode



HL8325G

Absolute Maximum Ratings

($T_C = 25^\circ\text{C}$)

Item	Symbol	Value	Unit
Optical output power	P_O	40	mW
Pulse optical output power	$P_{O(\text{pulse})}$	50 *	mW
Laser diode reverse voltage	$V_{R(\text{LD})}$	2	V
Photo diode reverse voltage	$V_{R(\text{PD})}$	30	V
Operating temperature	T_{opr}	-10 to +60	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +85	$^\circ\text{C}$

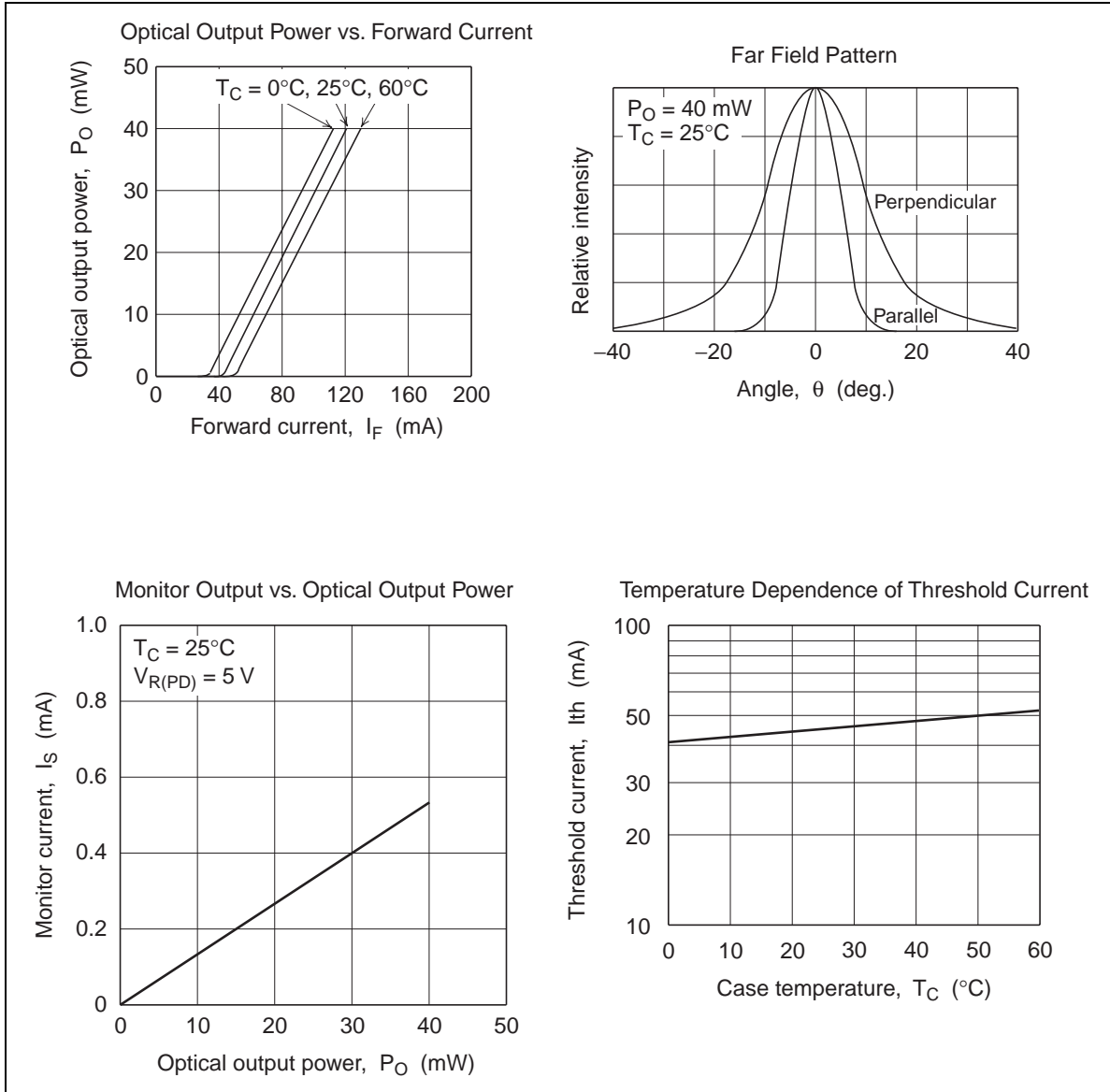
Note: Pulse condition : Pulse width = 1 μs , duty = 50%

Optical and Electrical Characteristics

($T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$)

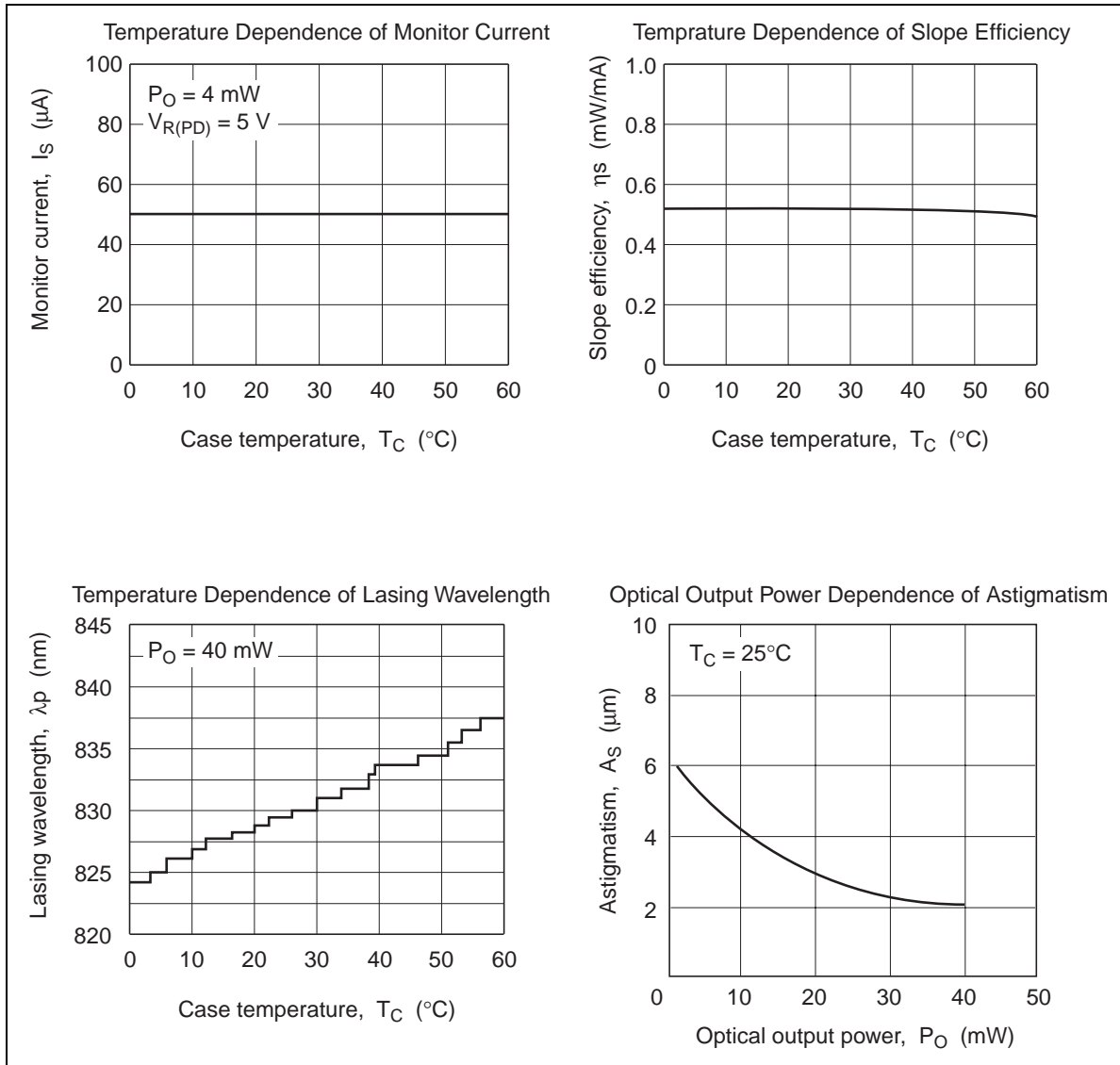
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Threshold current	I_{th}	—	40	70	mA	—
Slope efficiency	η_s	0.4	0.5	0.9	mW/mA	$24 \text{ (mW)} / (I_{(32\text{mW})} - I_{(8\text{mW})})$
Beam divergence parallel to the junction	$\theta_{//}$	7	10	14	deg.	$P_O = 40 \text{ mW}$, FWHM
Beam divergence perpendicular to the junction	θ_{\perp}	18	22	32	deg.	$P_O = 40 \text{ mW}$, FWHM
Asigmatism	A_s	—	5	—	μm	$P_O = 4 \text{ mW}$, NA = 0.4
Lasing wavelength	λ_p	820	830	840	nm	$P_O = 40 \text{ mW}$
Monitor current	I_s	20	40	130	μA	$P_O = 4 \text{ mW}$, $V_{R(\text{PD})} = 5 \text{ V}$

Typical Characteristic Curves



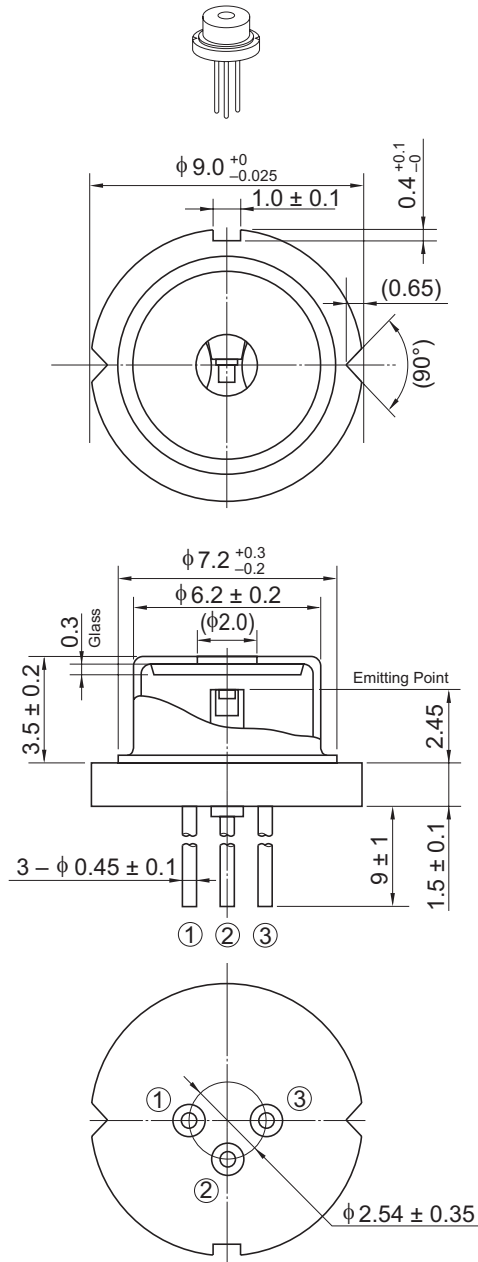
HL8325G

Typical Characteristic Curves (cont)



Package Dimensions

As of July, 2002
Unit: mm



OPJ Code	LD/G2
JEDEC	—
JEITA	—
Mass (reference value)	1.1 g

HL8325G

Cautions

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1. The laser light is harmful to human body especially to eye no matter what directly or indirectly. The laser beam shall be observed or adjusted through infrared camera or equivalent.
2. This product contains gallium arsenide (GaAs), which may seriously endanger your health even at very low doses. Please avoid treatment which may create GaAs powder or gas, such as disassembly or performing chemical experiments, when you handle the product.
When disposing of the product, please follow the laws of your country and separate it from other waste such as industrial waste and household garbage.
3. Definition of items shown in this CAS is in accordance with that shown in Opto Device Databook issued by OPJ unless otherwise specified.

Sales Offices



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